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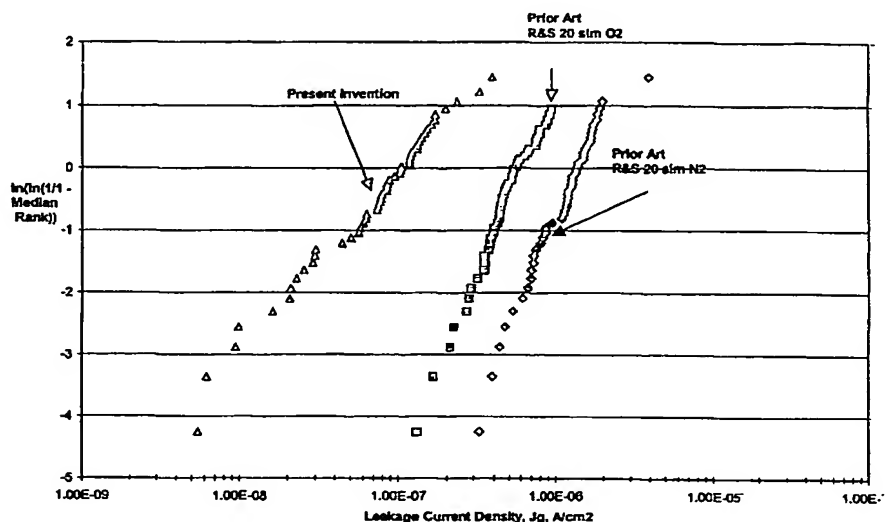
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(54) Title: **STEAM OXIDATION METHOD FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRICS WITH IMPROVED ELECTRICAL PROPERTIES**



Weibull plots for wet oxidation processes with and without ramp and stabilization step at 900°C

(57) Abstract: The present invention relates to the steam oxidation of silicon wafers to form thin gate and capacitor dielectrics with improved electrical properties. In the present invention, improved oxide properties are obtained in a single wafer Rapid Thermal Process ("RTP") by beginning steam oxidation without stabilizing the silicon wafer in dry oxygen.

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